

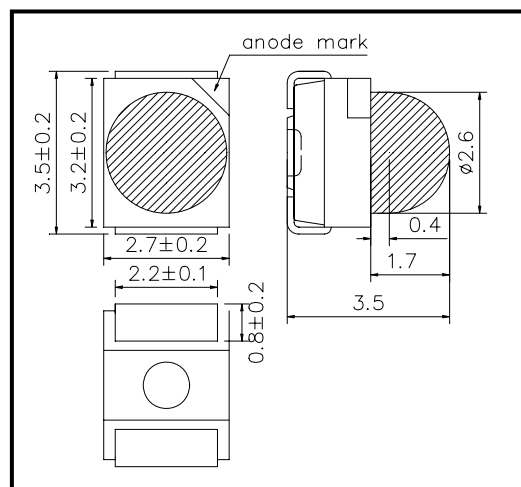
SMT750-23 Infrared TOP IR LED with lens

SMT750-23 consists of an AlGaAs LED mounted on the lead frame as TOP LED package with epoxy resin lens and is 35mW/sr typical. It emits a spectral band of radiation at 750nm.

◆Outer dimension (Unit:mm)

◆ Specifications

1) Product Name	TOP IR LED with lens
2) Type No.	SMT750-23
3) Chip	
(1) Chip Material	AlGaAs
(2) Peak Wavelength	750nm typ.
4) Package	
(1) Lead Frame Die	Silver Plated
(2) Package Resin	PPA Resin
(3) Lens	Epoxy Resin
(4) Diameter	Φ2.6mm



◆ Absolute Maximum Rating

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	190	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	500	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Operating Temperature	T _{OPR}	-20 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +80	°C	
Soldering Temperature	T _{SOL}	240	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 230°C

◆ Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =50mA		1.85	2.00	V
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =50mA	10.0	20.0		mW
Radiant Intensity	I _E	I _F =50mA	15.0	35.0		mW/sr
Peak Wavelength	λ _P	I _F =50mA	735	750	765	nm
Half Width	Δλ	I _F =50mA		35		nm
Viewing Half Angle	θ _{1/2}	I _F =50mA		±15		deg.
Rise Time	t _r	I _F =50mA		80		ns
Fall Time	t _f	I _F =50mA		80		ns

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.